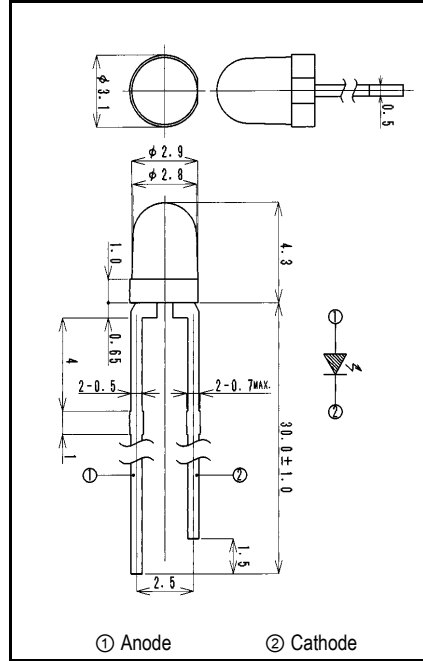
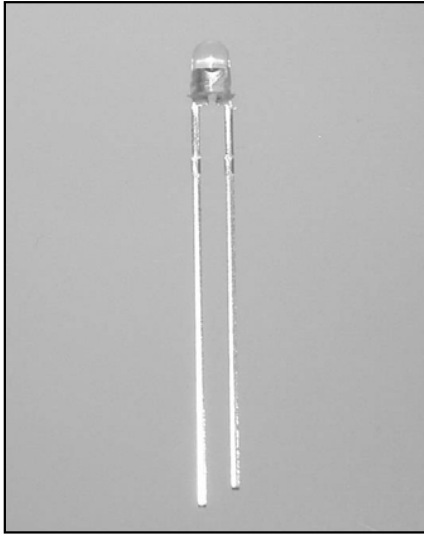


# LSF876C1

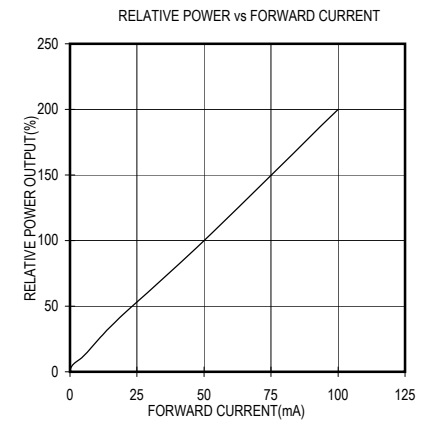
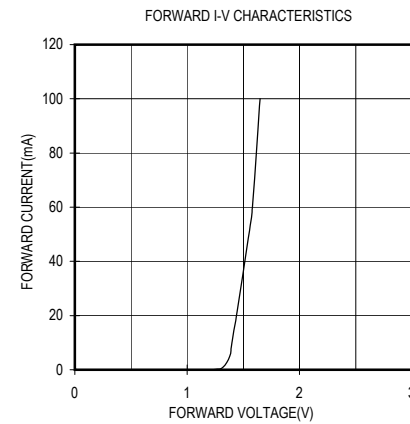
# Infrared Emitting Diode



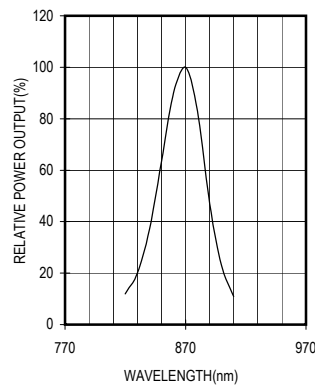
## 2. ELECTRICAL & OPTICAL CHARACTERISTICS (Ta=25°C)

ITEM	SYMBOL	CONDITIONS	MIN	TYP	MAX	UNIT
Power Output	PO	IF=50mA	8.0	18.0		mW
Forward Voltage	VF	IF=50mA		1.5	1.8	V
Reverse Current	IR	VR=5V			10	μA
Peak Wavelength	λp	IF=50mA		870		nm
Spectral Line Half Width	Δλ	IF=50mA		45		nm
Half Intensity Beam Angle	θ	IF=50mA		±20		deg.

- FEATURES**
- High-output Power
  - Compact
  - High Reliability
- APPLICATIONS**
- Optical Switches
  - Optical Sensors



## SPECTRAL OUTPUT

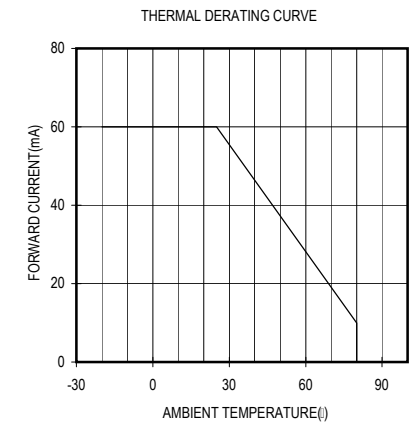
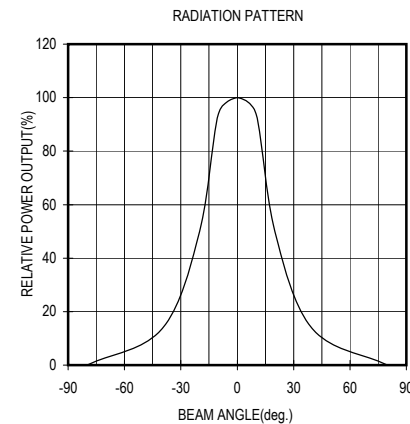


## 1. ABSOLUTE MAXIMUM RATINGS (Ta=25°C)

ITEM	SYMBOL	RATINGS	UNIT
Forward Current (DC)	IF	100	mA
Forward Current (Pulse)*1	IFP	1	A
Reverse Voltage	VR	5	V
Power Dissipation	PD	100	mW
Operating Temp.	Topr	-20 TO 80	°C
Storage Temp.	Tstg	-30 TO 100	°C
Junction Temp.	Tj	100	°C
Lead Soldering Temp.*2	Tls	260	°C

\*1:T<sub>w</sub>=10μs, T<sub>r</sub>=10ms

\*2:Time 5 Sec max, Position: Up to 3mm from the body



OPTRANS

To purchase this part contact  
Marktech Optoelectronics at  
**800.984.5337**

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www.marktechopt.com



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